

F7823-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)		
30	0.008 at V _{GS} = 10 V	13	6.1 nC		
30	0.011 at V _{GS} = 4.5 V	11	0.1 110		

FEATURES

- Halogen-free
- Trench Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

Notebook CPU Core
High-Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	$\mathbf{P} \mathbf{I}_{A} = 25$ °C, unles	s otherwise no	neu		
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	v		
Gate-Source Voltage	V _{GS}	± 20	1		
	T _C = 25 °C		13		
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	1-	10		
$Continuous Drain Current (1) = 150^{\circ} C)$	T _A = 25 °C	Ι _D	9 ^{b, c}		
	T _A = 70 °C		7 ^{b, c}	•	
Pulsed Drain Current	I _{DM}	45	A		
Outline Outline Duris Dials Outline	T _C = 25 °C	L.	3.7		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.0 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	7	
Avalanche Energy		E _{AS}	21	mJ	
	T _C = 25 °C		4.1		
Movimum Dower Dissinction	T _C = 70 °C	Pn	2.5	w	
Maximum Power Dissipation	T _A = 25 °C	'D	2.2 ^{b, c}	v	
	T _A = 70 °C	Ē	1.3 ^{b, c}	1	
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	- 55 to 150	°C		

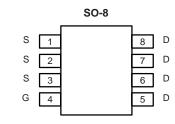
THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	39	55	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	25	29	0/10	

Notes:

a. Base on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s. d. Maximum under Steady State conditions is 85 °C/W.



Top View

RoHS

COMPLIANT



SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				1	1	1	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		26		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	5		- 6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	1000	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA	
Zero Gale voltage Drain Gurrent	IDSS	V_{DS} = 30 V, V_{GS} = 0 V, T_{J} = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, $V_{GS} = 10$ V	20			А	
	D	V _{GS} = 10 V, I _D = 10 A		0.008		6	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 9 A		0.011		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		50		S	
Dynamic ^b	11						
Input Capacitance	C _{iss}			800		pF	
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		165			
Reverse Transfer Capacitance	C _{rss}			73			
	$V_{DS} = 15 \text{ V}, \text{ V}_{CS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ V}, $	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		15	23		
Total Gate Charge				6.8	10.2	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 10 \text{ A}$		2.5			
Gate-Drain Charge	Q _{gd}			2.3			
Gate Resistance	R _g	f = 1 MHz	0.36	1.8	3.6	Ω	
Turn-On Delay Time	t _{d(on)}			16	23	-	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		12	16		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 9 Å, V_{GEN} = 4.5 V, R_g = 1 Ω		16	22		
Fall Time	t _f			10	18		
Turn-On Delay Time	t _{d(on)}			8	16	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		10	20	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		16	22		
Fall Time	t _f	-		8	15		
Drain-Source Body Diode Characterist	ics				•	1	
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			10		
Pulse Diode Forward Current ^a	I _{SM}			1	50	A	
Body Diode Voltage	V _{SD}	I _S = 9 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			6	12	nC	
Reverse Recovery Fall Time	t _a	$I_F = 9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 ^\circ\text{C}$		8		1	
Reverse Recovery Rise Time	t _b			7		ns	

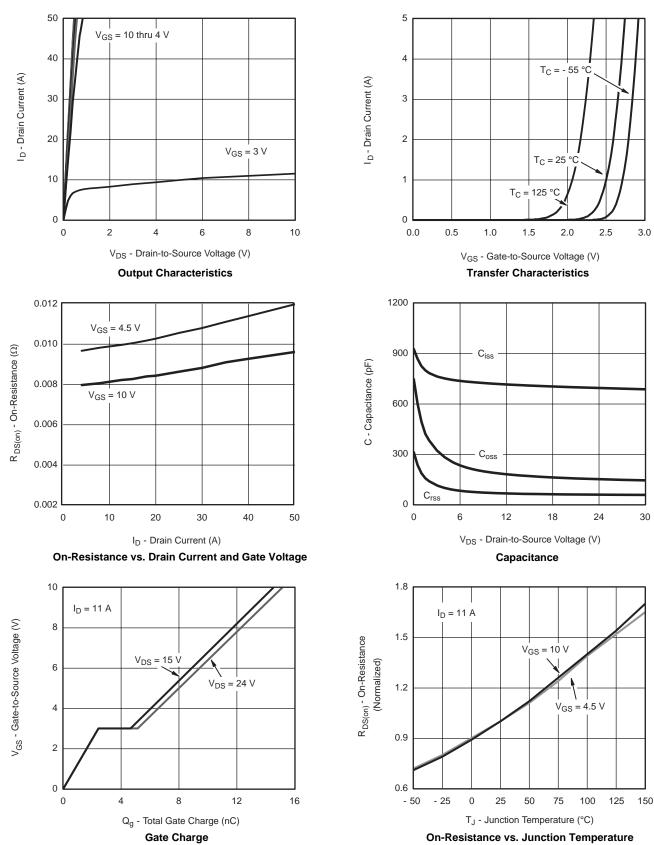
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

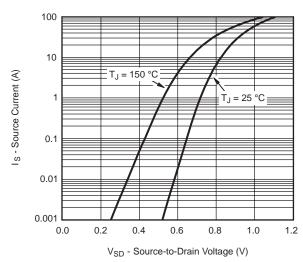




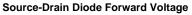


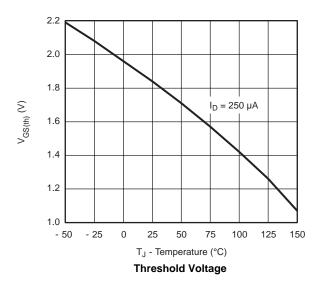
服务热线:400-655-8788

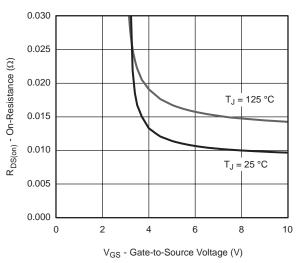




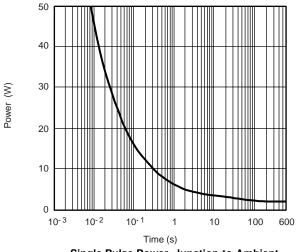
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



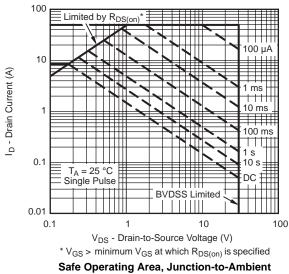




On-Resistance vs. Gate-to-Source Voltage

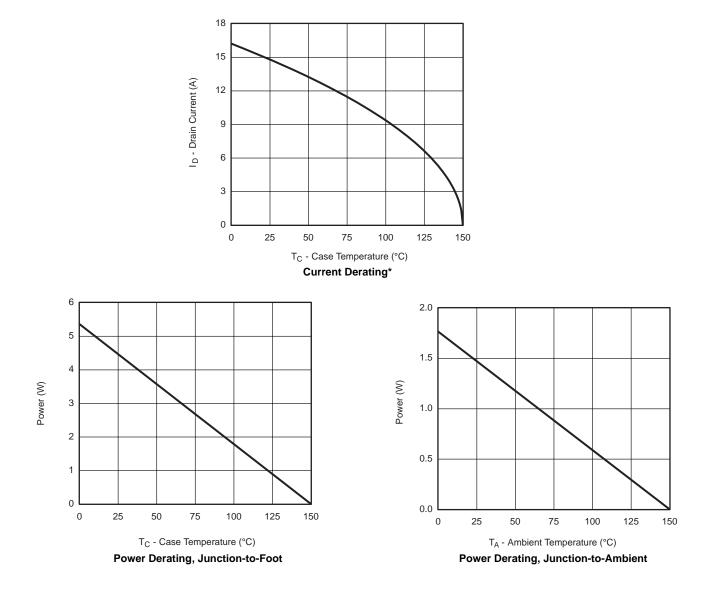






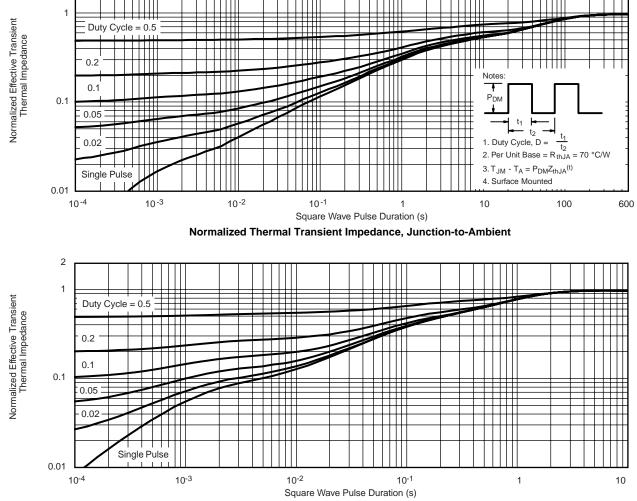


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

2



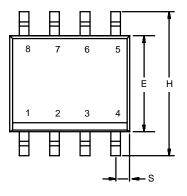
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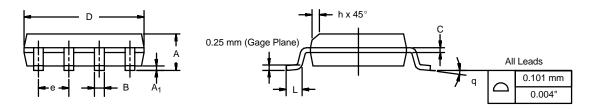
Normalized Thermal Transient Impedance, Junction-to-Foot

<u>VBsemi</u> www.VBsemi.com



SOIC (NARROW): 8-LEAD

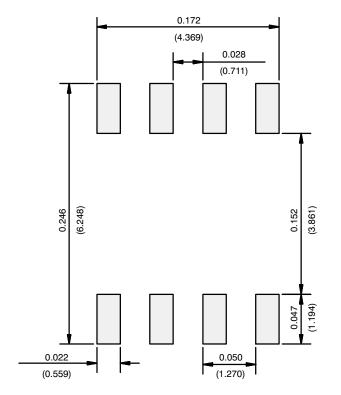




	MILLIMETERS		INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050	0.050 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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